

# GAU212S-15255 Universal Gate Drive Prototype Board



Size : 60 x 120 x 40t

Gate Driver : VLA502-01R

## FEATURE

- >Built in the isolated DC-DC converter for gate drive
- >Output peak current is +/-12A(max)
- >Electrical isolation voltage is 2500Vrms (for 1 minute)
- >Two way power supply system for drivers and input signal (VD=15V , VIN=5V)
- >CMOS compatible input interface

## RECOMMENDED IGBT MODULES

MITSUBISHI NFH series IGBT modules  
VCES = 600V series ~ 400A class  
VCES = 1200V series ~ 600A class

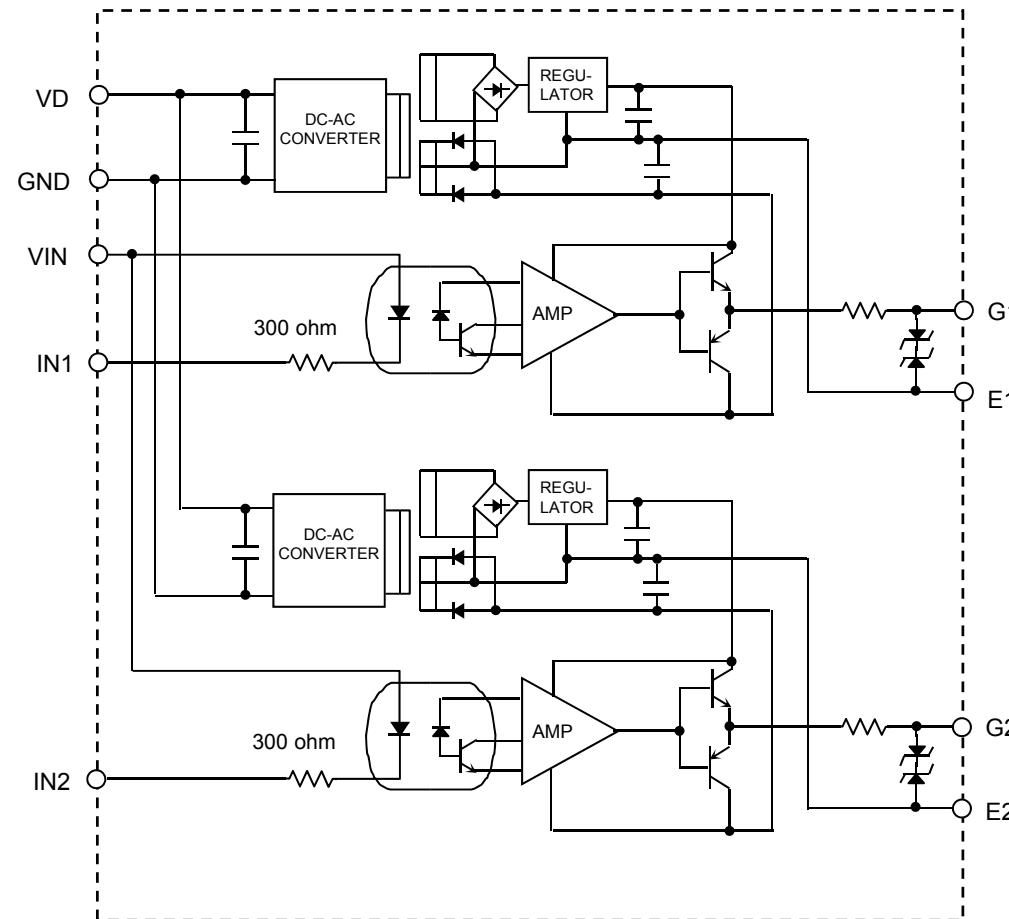
MITSUBISHI NF series IGBT modules  
VCES = 600V series ~ 600A class  
VCES = 1200V series ~1400A class



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## BLOCK DIAGRAM



## MAXIMUM RATINGS

(unless otherwise noted, Ta=25C)

Symbol	Parameter	Conditions	Ratings	Unit
VD	Supply voltage	DC	16.5	V
VI	Input signal voltage	Applied between VIN – IN1,2 50% Duty cycle , pulse width 1ms	-1 ~+7	V
IOHP	Output peak current	Pulse width 2us	-12	A
			12	A
Viso	Isolation voltage	Sine wave voltage 60Hz, for 1min	2500	Vrms
Topr	Operating temperature	No condensation allowable	-20 ~ 60	deg C
Tstg	Storage temperature	No condensation allowable	-25 ~ 85	deg C
Idrive	Gate drive current	Gate average current (Per one circuit)	210	mA

## ELECTRICAL CHARACTERISTICS

( unless otherwise noted, Ta=25C, VD=15V)

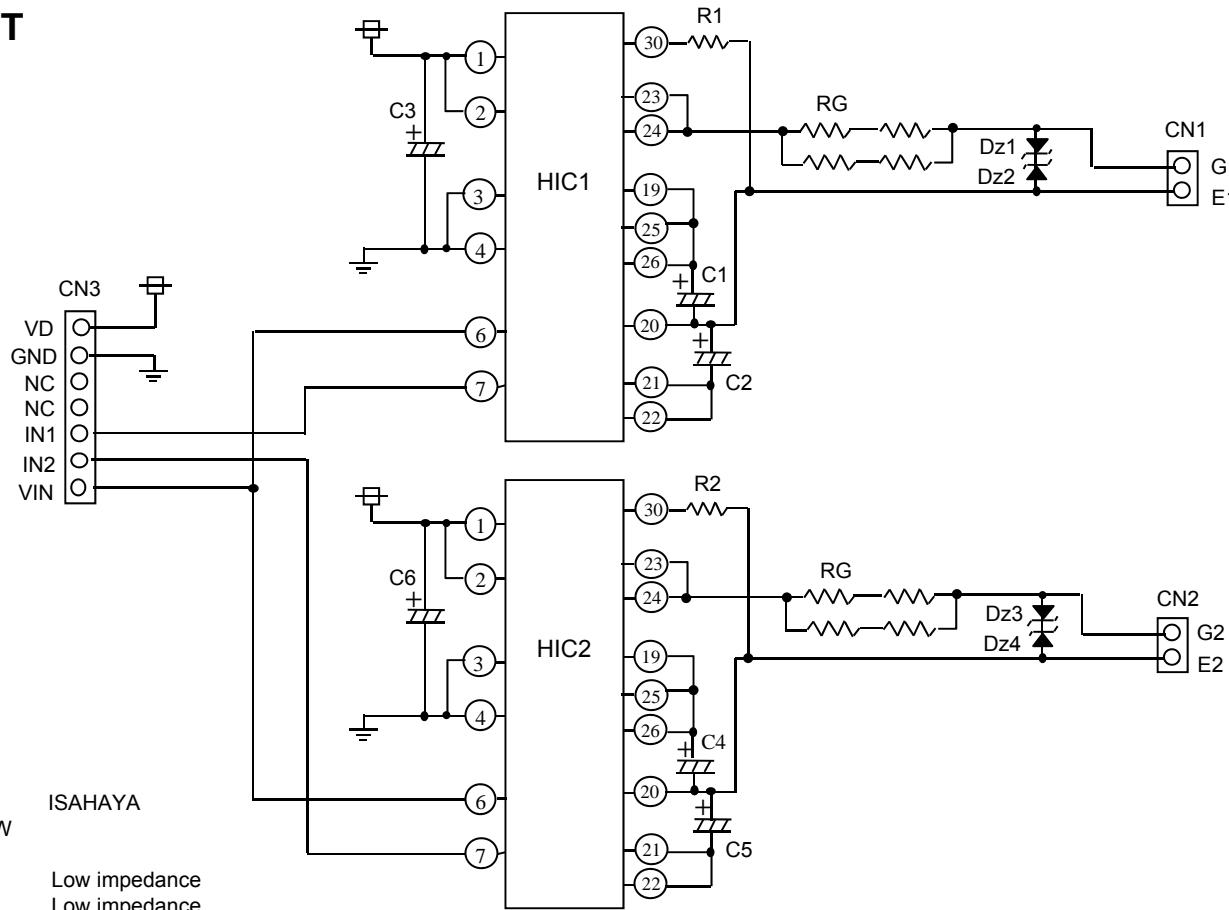
Symbol	Parameter	Conditions	Limits			Unit
			Min	Typ	Max	
VD	Supply voltage	Recommended range	14.2	15	15.8	V
VIN	Pull-up voltage on input side	Recommended range	4.75	5	5.25	V
IIH	"H" input signal current	Recommended range	9.5	10	14	mA
f	Switching frequency	Recommended range	-	-	60	kHz
RG	Gate resistance	Recommended range	1	-	-	ohm
VOH	Plus bias voltage	-	14	15.5	16.5	V
VOL	Minus bias voltage	-	-11	-8	-5.5	V
tPLH	"L-H" propagation time	IIH = 10mA	-	0.4	0.65	us
tPHL	"H-L" propagation time	IIH = 10mA	-	0.4	0.65	us



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## INNER CIRCUIT



HIC1,2  
DZ1,2,3,4  
RG  
C1,2,4,5  
C3,6  
R1,2  
CN1,2  
CN3

VLA502-01R  
Vz=18V, 500mW  
Gate Resistor  
1000 $\mu$ F, 35V  
100 $\mu$ F, 50V  
4.7k ohm, 250mW  
B2B-XH-A  
B7B-XH-A

ISAHAYA  
Low impedance  
Low impedance  
JST  
JST

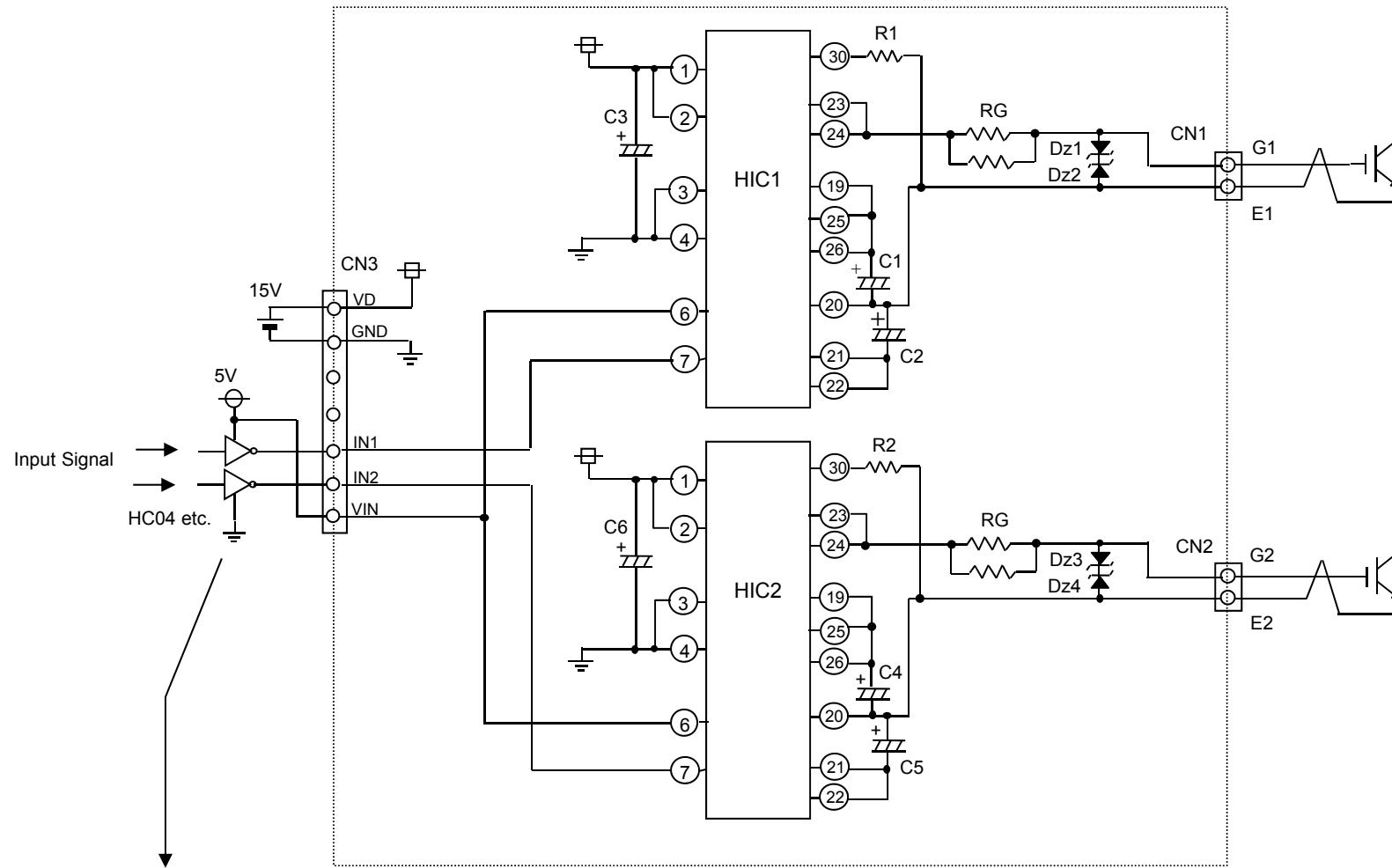
\*\*) Gate Resistor is not installed at the time of shipment.  
Please solder the chosen resistor.



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## APPLICATION EXAMPLE



\*\*Open-collector(drain) type is not recommended.



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## PRECAUTION

### (1) Confirmation of gate average current

The maximum rating of output current capacity per one circuit of the gate power supply built-in this product is 210mA. (\*)  
Therefore the gate average current must be less than 210mA.

Please calculate the gate average current by the following expression.

$$I_{drive} = (Q_1 + I_{Q2}) \times f$$

$I_{drive}$  : Gate average current

$Q_1$  : Gate charge on plus bias (Please read it from data sheet of IGBT)

$Q_2$  : Gate charge on minus bias (Please read it from data sheet of IGBT)

$f$  : Switching frequency

### (2) Electric power setting of gate resistance

At the time of the choice of gate resistance, please choose the resistance which can permit the electric power by the following calculation.

$$P_d = I_{drive} \times 25 + \text{margin}$$

$P_d$  : Total allowable power loss of gate resistance

$I_{drive}$  : Gate average current

25 : Total output voltage of gate power supply

(\*) Please refer to derating curve of VLA502 data sheet.



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## Part arrangement & Size

